

## NTE573 Schottky Barrier Rectifier

### **Description:**

The NTE573 is an axial lead metal-to-silicon power diode using the Schottky Barrier principle. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. This device is ideally suited for use in low-voltage, high-frequency inverters, as free wheeling diodes, and polarity protection diodes.

### **Features:**

- Low Forward Voltage
- Low Power Loss
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction
- High Efficiency
- High Switching Capability

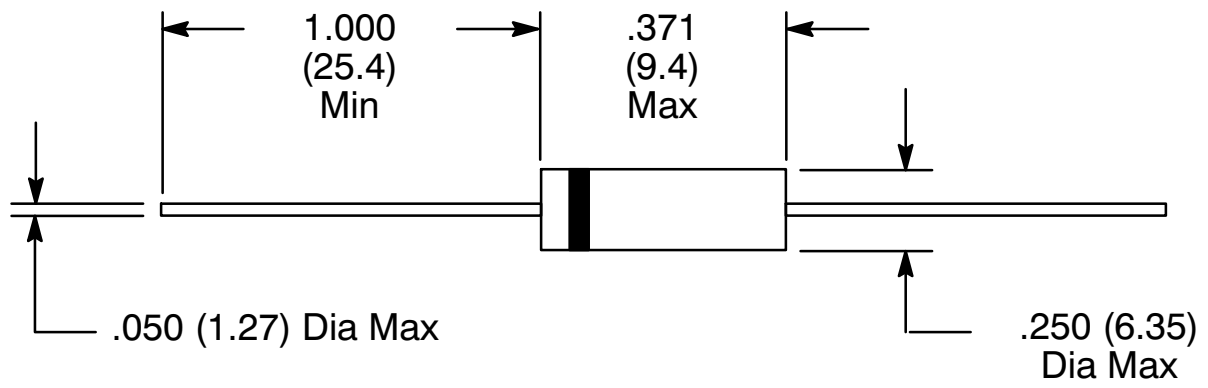
### **Absolute Maximum Ratings:**

Peak Repetitive Reverse Voltage, $V_{RRM}$ .....	60V
Working Peak Reverse Voltage, $V_{RWM}$ .....	60V
DC Blocking Voltage, $V_R$ .....	60V
RMS Reverse Voltage, $V_{R(RMS)}$ .....	42V
Average Forward Rectified Current, $I_O$ .....	5A
Non-Repetitive Peak Surge Current, $I_{FSM}$ (Surge applied at rated load conditions half-wave, single phase, 60Hz, $T_L = +70^\circ\text{C}$ ) .	150A
Operating Junction Temperature Range, $T_J$ .....	-65° to +125°C
Storage Temperature Range, $T_{stg}$ .....	-65° to +125°C

### **Electrical Characteristics:**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Instantaneous Forward Voltage	$V_F$	$I_F = 5A$	-	-	0.70	V
		$I_F = 15A$	-	-	0.95	V
Instantaneous Reverse Current	$I_R$	$V_R = 60V, T_L = +25^\circ\text{C}$	-	-	5	mA
		$V_R = 60V, T_L = +100^\circ\text{C}$	-	-	50	mA
Junction Capacitance	$C_P$	Note 1	-	400	-	pF

Note 1. Measured at 1MHz and applied reverse voltage of 4 volts.



Color Band Denotes Cathode